



SUNMATE

8A05 - 8A10

AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V

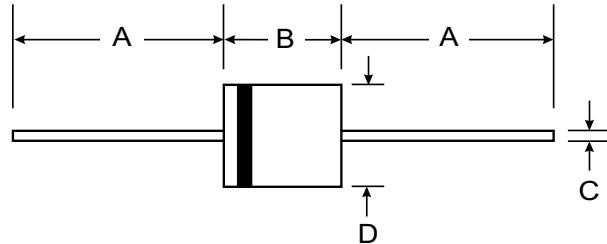
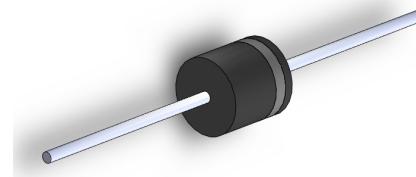
CURRENT: 8.0 A

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: R-6,
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Mounting Position: Any
- Marking: Type Number
- Weight: 2.1 grams (approx.)



R-6		
Dim	Min	Max
A	25.4	—
B	8.6	9.1
C	1.2	1.3
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	8A05	8A1	8A2	8A4	8A6	8A8	8A10	Unit			
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	V			
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	V			
Average Rectified Output Current (Note 1) $\quad @T_A = 50^\circ\text{C}$	I_o	8.0							A			
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	600							A			
Forward Voltage $\quad @I_F = 8.0\text{A}$	V_{FM}	1.0							V			
Peak Reverse Current $\quad @T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage $\quad @T_A = 100^\circ\text{C}$	I_{RM}	10 100							μA			
Typical Junction Capacitance (Note 2)	C_j	150			80			pF				
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	10							$^\circ\text{C/W}$			
Operating Temperature Range	T_j	-50 to +150							$^\circ\text{C}$			
Storage Temperature Range	T_{STG}	-50 to +150							$^\circ\text{C}$			

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.



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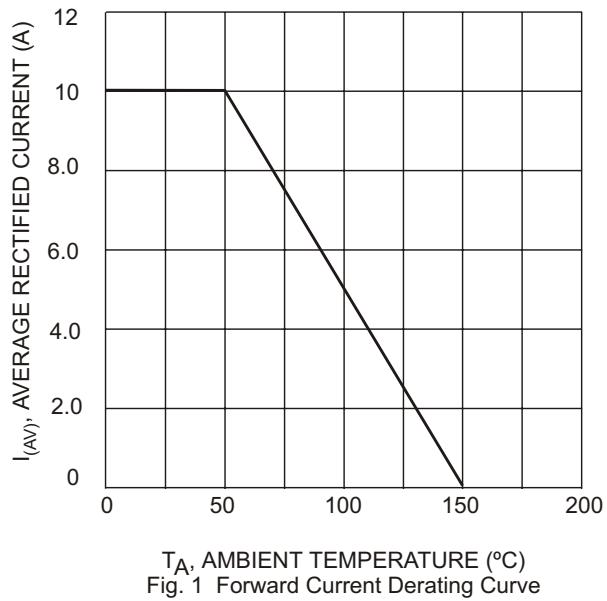


Fig. 1 Forward Current Derating Curve

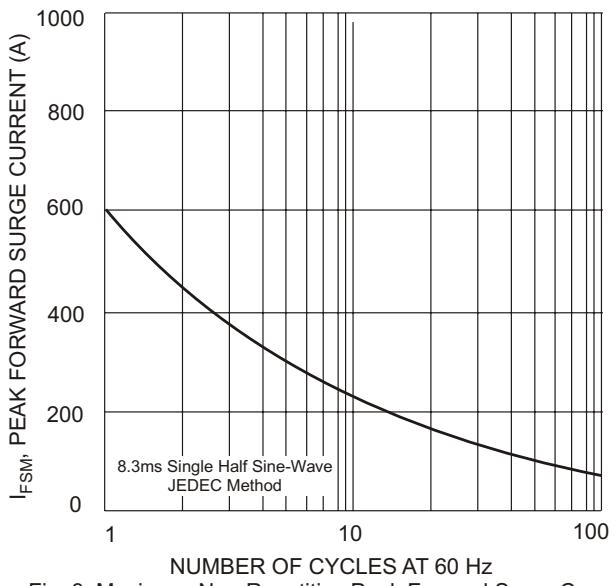


Fig. 3 Maximum Non-Repetitive Peak Forward Surge Current

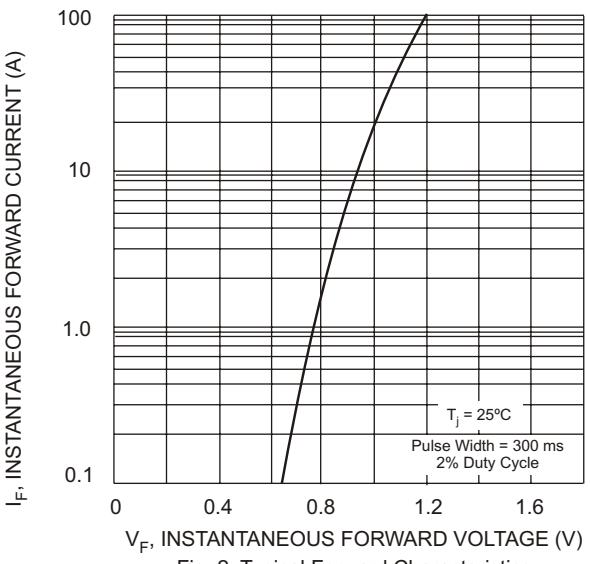


Fig. 2 Typical Forward Characteristics

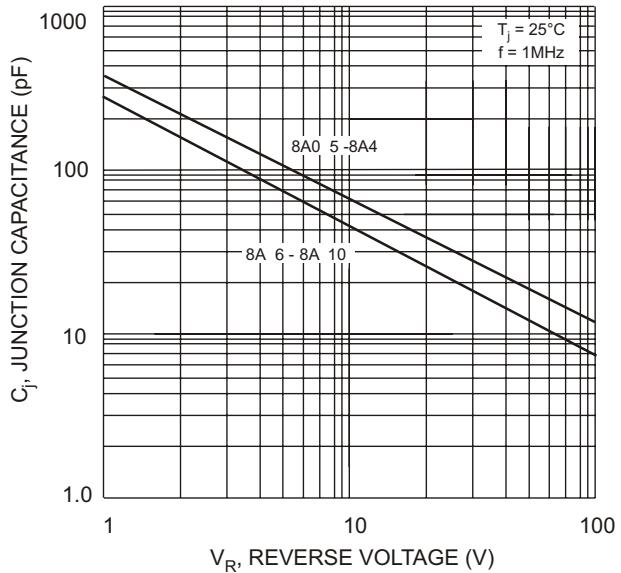


Fig. 4 Typical Junction Capacitance